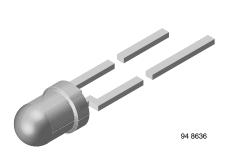
**Vishay Semiconductors** 



BoHS

COMPLIANT

# High Power Infrared Emitting Diode, RoHS Compliant, 940 nm, GaAlAs/GaAs



## FEATURES

- · Package type: leaded
- Package form: T-1
- Dimensions (in mm):  $\varnothing$  3
- Peak wavelength:  $\lambda_p = 940 \text{ nm}$
- High reliability
- · High radiant power
- · High radiant intensity
- Angle of half intensity:  $\phi = \pm 25^{\circ}$
- · Low forward voltage
- Suitable for high pulse current operation
- · Good spectral matching with Si photodetectors
- Package matches with detector TEFT4300
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

## APPLICATIONS

- Infrared remote control units
- Free air transmission systems
- · Infrared source for optical counters and card readers

## DESCRIPTION

TSAL4400 is an infrared, 940 nm emitting diode in GaAlAs/GaAs technology with high radiant power molded in a blue-gray plastic package.

### **PRODUCT SUMMARY**

| COMPONENT | l <sub>e</sub> (mW/sr) | φ <b>(deg)</b> | λ <sub>P</sub> (nm) | t <sub>r</sub> (ns) |  |
|-----------|------------------------|----------------|---------------------|---------------------|--|
| TSAL4400  | 30                     | ± 25           | 940                 | 800                 |  |

#### Note

Test conditions see table "Basic Characteristics"

# 

| ORDERING CODE | PACKAGING | REMARKS                      | PACKAGE FORM |
|---------------|-----------|------------------------------|--------------|
| TSAL4400      | Bulk      | MOQ: 5000 pcs, 5000 pcs/bulk | T-1          |

### Note

MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS            |   |                   |               |      |  |
|-------------------------------------|---|-------------------|---------------|------|--|
| PARAMETER                           | TEST CONDITION                            | SYMBOL            | VALUE         | UNIT |  |
| Reverse voltage                     |   | V <sub>R</sub>    | 5             | V    |  |
| Forward current                     |   | l <sub>F</sub>    | 100           | mA   |  |
| Peak forward current                | $t_p/T = 0.5, t_p = 100 \ \mu s$          | I <sub>FM</sub>   | 200           | mA   |  |
| Surge forward current               | t <sub>p</sub> = 100 μs                   | I <sub>FSM</sub>  | 1.5           | А    |  |
| Power dissipation                   |   | Pv                | 160           | mW   |  |
| Junction temperature                |   | Тj                | 100           | °C   |  |
| Operating temperature range         |   | T <sub>amb</sub>  | - 40 to + 85  | °C   |  |
| Storage temperature range           |   | T <sub>stg</sub>  | - 40 to + 100 | °C   |  |
| Soldering temperature               | $t \leq$ 5 s, 2 mm from case              | T <sub>sd</sub>   | 260           | °C   |  |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm,<br>soldered on PCB | R <sub>thJA</sub> | 300           | K/W  |  |

#### Note

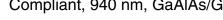
 $T_{amb}$  = 25 °C, unless otherwise specified

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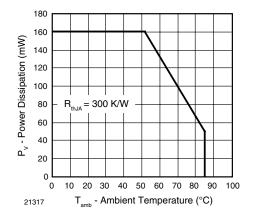


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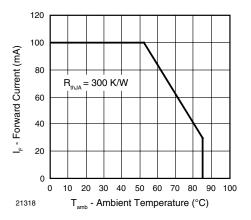


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS                     |   |                  |      |       |      |       |
|---|---|------------------|------|-------|------|-------|
| PARAMETER                                 | TEST CONDITION                                  | SYMBOL           | MIN. | TYP.  | MAX. | UNIT  |
| Forward voltage                           | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms | V <sub>F</sub>   |      | 1.35  | 1.6  | V     |
|   | $I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$   | V <sub>F</sub>   |      | 2.6   | 3    | V     |
| Temperature coefficient of V <sub>F</sub> | I <sub>F</sub> = 1 mA                           | TK <sub>VF</sub> |      | - 1.8 |      | mV/K  |
| Reverse current                           | V <sub>R</sub> = 5 V                            | I <sub>R</sub>   |      |       | 10   | μΑ    |
| Junction capacitance                      | V <sub>R</sub> = 0 V, f = 1 MHz, E = 0          | Cj               |      | 25    |      | pF    |
| Radiant intensity                         | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$     | l <sub>e</sub>   | 16   | 30    | 80   | mW/sr |
|   | $I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$   | l <sub>e</sub>   | 135  | 240   |      | mW/sr |
| Radiant power                             | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$     | φ <sub>e</sub>   |      | 35    |      | mW    |
| Temperature coefficient of $\phi_{e}$     | I <sub>F</sub> = 20 mA                          | TKφe             |      | - 0.6 |      | %/K   |
| Angle of half intensity                   |   | φ                |      | ± 25  |      | deg   |
| Peak wavelength                           | I <sub>F</sub> = 100 mA                         | λ <sub>p</sub>   |      | 940   |      | nm    |
| Spectral bandwidth                        | I <sub>F</sub> = 100 mA                         | Δλ               |      | 50    |      | nm    |
| Temperature coefficient of $\lambda_p$    | I <sub>F</sub> = 100 mA                         | ΤΚλ <sub>ρ</sub> |      | 0.2   |      | nm/K  |
| Rise time                                 | l <sub>F</sub> = 100 mA                         | tr               |      | 800   |      | ns    |
| Fall time                                 | l <sub>F</sub> = 100 mA                         | t <sub>f</sub>   |      | 800   |      | ns    |
| Virtual source diameter                   | Method: 63 % encircled energy                   | d                |      | 1.9   |      | mm    |

### Note

 $T_{amb}$  = 25 °C, unless otherwise specified

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### **BASIC CHARACTERISTICS**

 $T_{amb} = 25 \ ^{\circ}C$ , unless otherwise specified

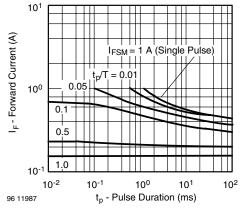


Fig. 3 - Pulse Forward Current vs. Pulse Duration

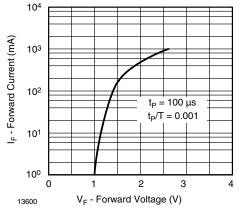


Fig. 4 - Forward Current vs. Forward Voltage

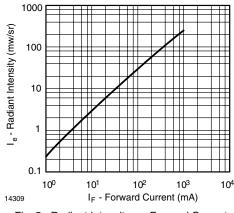


Fig. 5 - Radiant Intensity vs. Forward Current

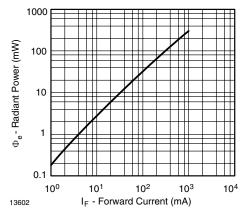


Fig. 6 - Radiant Power vs. Forward Current

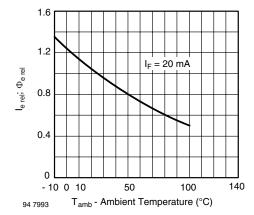


Fig. 7 - Rel. Radiant Intensity/Power vs. Ambient Temperature

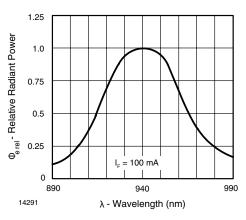


Fig. 8 - Relative Radiant Power vs. Wavelength



# **TSAL4400**

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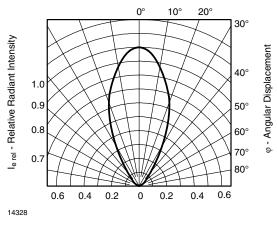
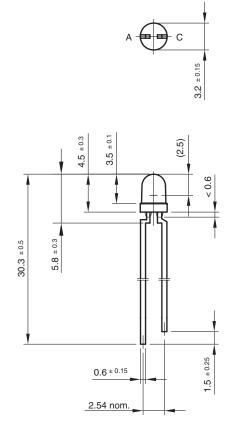
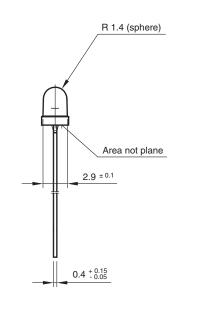


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

### **PACKAGE DIMENSIONS** in millimeters







according to DIN specifications

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